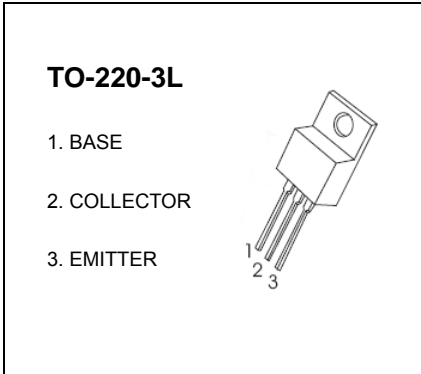




**TO-220-3L Plastic-Encapsulate Transistors**

**2SC2073** TRANSISTOR (NPN)



**FEATURES**

- Wide safe Operating Area.
- Complementary to 2SA940

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	1.5	A
P <sub>C</sub>	Collector Power Dissipation	1.5	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	150			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	150			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0			10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			10	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A	40		140	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =0.5A, I <sub>B</sub> =50mA			1.5	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A	0.65		0.85	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A		4		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		35		pF